NSN 5961-00-953-4494

A110a0

Unitized Semiconductor Devices - Page 1 of 1



View Online at https://aerobasegroup.com/nsn/5961-00-953-4494 **Inclosure Material:** Metal **Overall Length:** Between 0.150 inches and 0.260 inches Overall Diameter: Between 0.335 inches and 0.370 inches **Function For Which Designed:** Amplifier **Component Name And Quantity:** 2 transistor **Mounting Method: Terminal Semiconductor Material:** Silicon all transistor Voltage Rating In Volts Per Characteristic: 100.0 collector to base voltage/static/emitter open all transistor and 60.0 collector to emitter voltage/static/base open all transistor and 7.0 emitter to base voltage, static, collector open all transistor and 80.0 collector-to-emitter, resistance between base and emitter all transistor **Current Rating Per Characteristic:** 500.00 milliamperes source cutoff current all transistor **Power Rating Per Characteristic:** 1.6 watts small-signal input power, common-collector absolute 2nd transistor **Maximum Operating Tempurature Per Measurement Point:** 200.0 degrees celsius junction **Special Features:** All transistor junction pattern arrangement: npn **Terminal Type And Quantity:** 6 uninsulated wire lead Shelf Life: N/a **Unit Of Measure: Demilitarization:** No Fiig: